ESD9L, SESD9L Series

ESD Protection Diode
Ultra−Low Capacitance

The ESD9L Series is designed to protect voltage sensitive components that require ultra−low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Specification Features:

- Ultra Low Capacitance 0.5 pF
- Low Clamping Voltage
- Small Body Outline Dimensions:
  0.039″ x 0.024″ (1.00 mm x 0.60 mm)
- Low Body Height: 0.016″ (0.4 mm)
- Stand−off Voltage: 3.3 V, 5 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000−4−2 Level 4 ESD Protection
- S and SZ Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic
Epoxy Meets UL 94 V−0
LEAD FINISH: 100% Matte Sn (Tin)
MOUNTING POSITION: Any
QUALIFIED MAX REFLOW TEMPERATURE: 260°C
Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
IEC 61000−4−2 (ESD)	Contact Air		±10 ±15	kV
Total Power Dissipation on FR−5 Board (Note 1) @ T_A = 25°C		P_D	150	mW
Storage Temperature Range		T_{stg}	−55 to +150	°C
Junction Temperature Range		T_J	−55 to +150	°C
Lead Solder Temperature − Maximum (10 Second Duration)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 = 1.0 x 0.75 x 0.62 in.

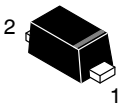
See Application Note AND8308/D for further description of survivability specs.

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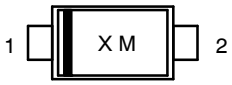


PIN 1. CATHODE
2. ANODE



SOD−923
CASE 514AB

MARKING DIAGRAM



X = Specific Device Code
M = Date Code

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
ESD9LxxxST5G	SOD−923 (Pb−Free)	8000/Tape & Reel
SESD9LxxxST5G	SOD−923 (Pb−Free)	8000/Tape & Reel
SZESD9LxxxST5G	SOD−923 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics tables starting on page 2 of this data sheet.

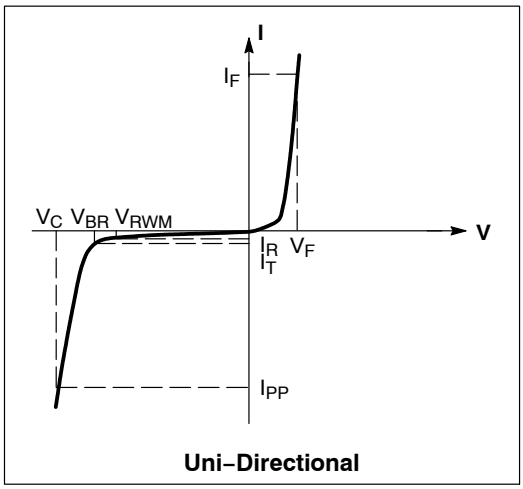
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ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Max. Capacitance @ V_R = 0 and f = 1.0 MHz

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.0 V Max. @ I_F = 10 mA for all types)

Device*	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)	I_T	C (pF)		V_C (V) @ I_{PP} = 1 A	V_C
		Max	Max	Min	mA	Typ	Max	Max	Per IEC61000−4−2 (Note 4)
ESD9L3.3ST5G	6**	3.3	1.0	4.8	1.0	0.5	0.9	9.0	Figures 1 and 2 See Below
ESD9L5.0ST5G	D	5.0	1.0	5.4	1.0	0.5	0.9	9.8	Figures 1 and 2 See Below

* Includes S and SZ-prefix devices where applicable.
**Rotated 180°.

2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.
3. Surge current waveform per Figure 5.
4. For test procedure see Figures 3 and 4 and Application Note AND8307/D.

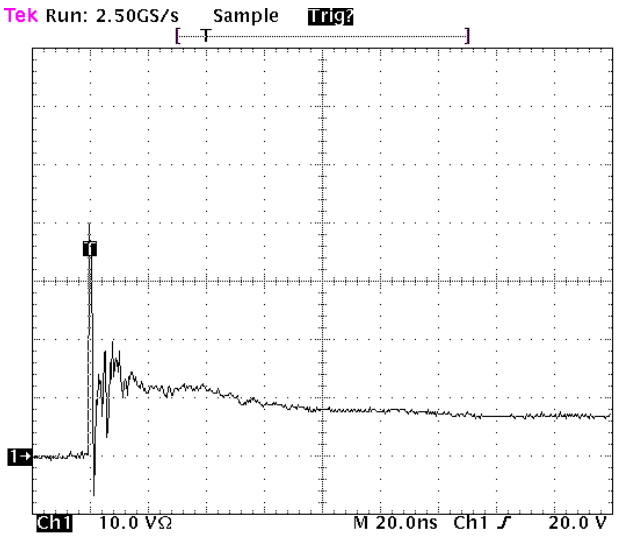


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000−4−2

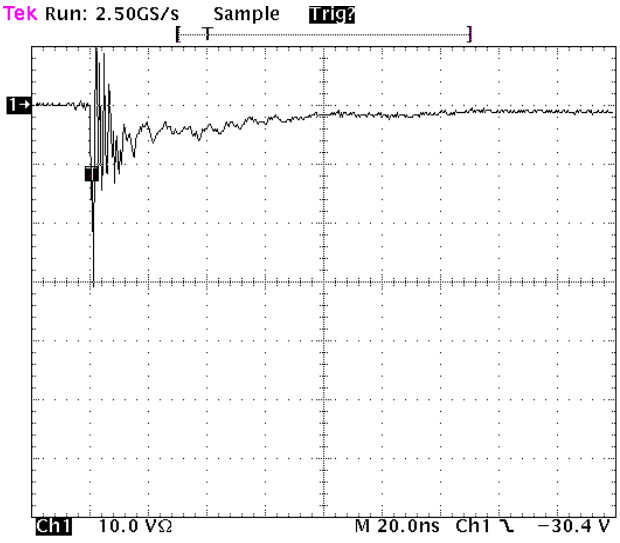


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000−4−2

IEC 61000−4−2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

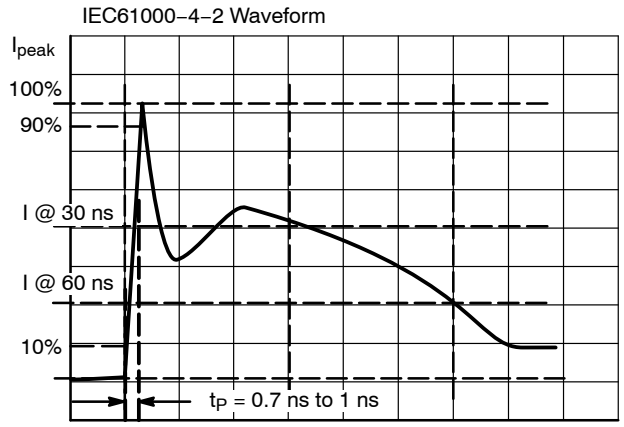


Figure 3. IEC61000−4−2 Spec

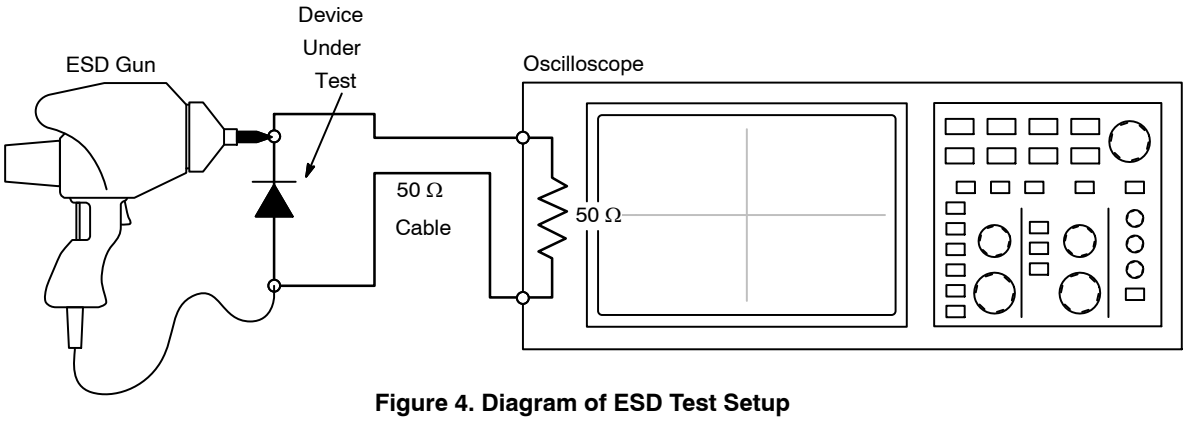


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D − Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000−4−2 waveform. Since the IEC61000−4−2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

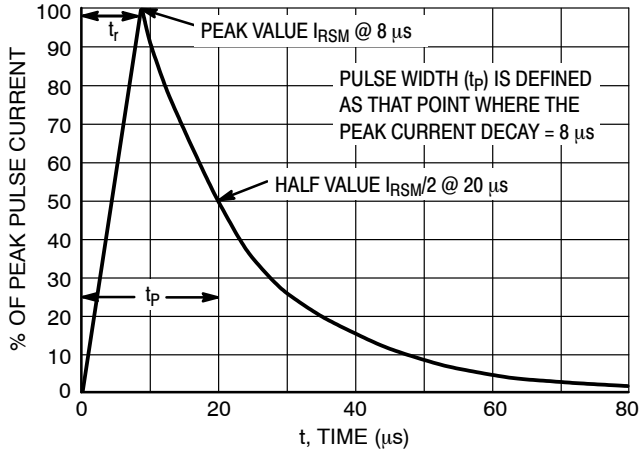
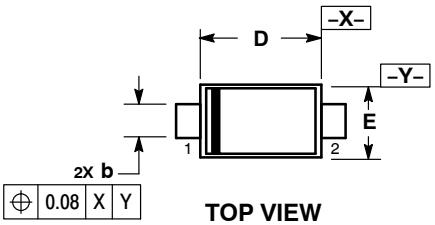


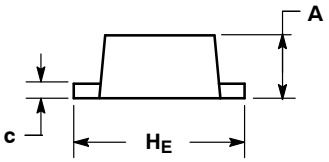
Figure 5. 8 X 20 μs Pulse Waveform

PACKAGE DIMENSIONS

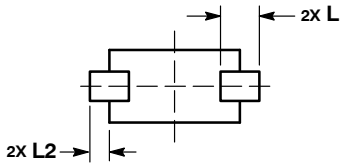
SOD−923
CASE 514AB
ISSUE C



TOP VIEW



SIDE VIEW

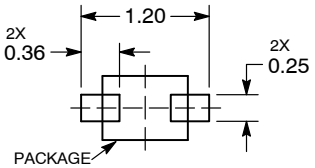


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
H_E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.19 REF			0.007 REF		
L2	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

See Application Note AND8455/D for more mounting details

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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